

Silicon PNP Power Transistors

2N6285 2N6286 2N6287

DESCRIPTION

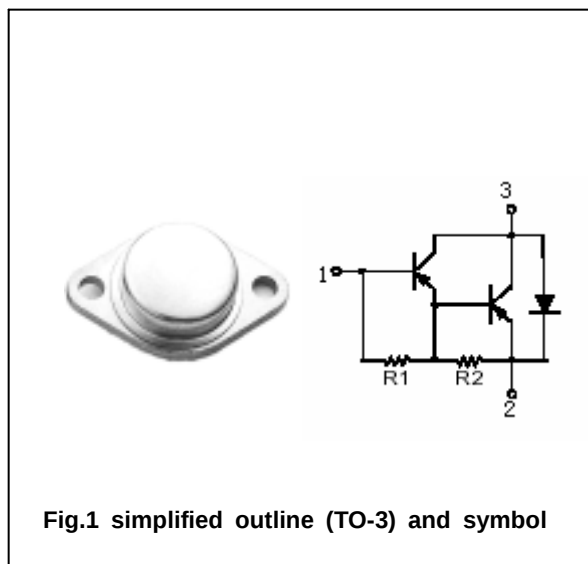
- With TO-3 package
- Complement to type 2N6282/6283/6284
- High DC current gain
- DARLINGTON

APPLICATIONS

- For use in general-purpose amplifier and low-frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6285	-60	V
		2N6286	-80	
		2N6287	-100	
V_{CEO}	Collector-emitter voltage	2N6285	-60	V
		2N6286	-80	
		2N6287	-100	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-20	A
I_{CM}	Collector current-peak		-40	A
I_B	Base current		-0.5	A
P_D	Total Power Dissipation	$T_C = 25$	160	W
T_j	Junction temperature		200	
T_{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.09	/W

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6285	$I_C = -0.2A ; I_B = 0$	-60			V
		2N6286		-80			
		2N6287		-100			
$V_{CEsat-1}$	Collector-emitter saturation voltage		$I_C = -10A ; I_B = -40mA$			-2.0	V
$V_{CEsat-2}$	Collector-emitter saturation voltage		$I_C = -20A ; I_B = -200mA$			-3.0	V
V_{BEsat}	Base-emitter saturation voltage		$I_C = -20A ; I_B = -200mA$			-4.0	V
V_{BE}	Base-emitter on voltage		$I_C = -10A ; V_{CE} = -3V$			-2.8	V
I_{CEO}	Collector cut-off current	2N6285	$V_{CE} = -30V ; I_B = 0$			-1.0	mA
		2N6286	$V_{CE} = -40V ; I_B = 0$				
		2N6287	$V_{CE} = -50V ; I_B = 0$				
I_{CEX}	Collector cut-off current	2N6285	$V_{CE} = -60V ; V_{BE} = -1.5V$ $T_C = 150$			-0.5 -5.0	mA
		2N6286	$V_{CE} = -80V ; V_{BE} = -1.5V$ $T_C = 150$			-0.5 -5.0	
		2N6287	$V_{CE} = -100V ; V_{BE} = -1.5V$ $T_C = 150$			-0.5 -5.0	
I_{EBO}	Emitter cut-off current		$V_{EB} = -5V ; I_C = 0$			-2.0	mA
h_{FE-1}	DC current gain		$I_C = -10A ; V_{CE} = -3V$	750		18000	
h_{FE-2}	DC current gain		$I_C = -20A ; V_{CE} = -3V$	100			
C_{OB}	Output capacitance		$I_E = 0 ; V_{CB} = -10V ; f = 1MHz$			600	pF

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PACKAGE OUTLINE

